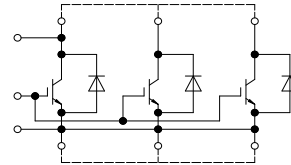


IHM-B Modul mit soft schaltendem Trench-IGBT4
IHM-B module with soft-switching Trench-IGBT4

Vorläufige Daten / Preliminary Data



external connection
(to be done)

$V_{CES} = 1700V$
 $I_{C\ nom} = 3600A / I_{CRM} = 7200A$

Typische Anwendungen

- Hochleistungsumrichter
- Motorantriebe

Typical Applications

- High Power Converters
- Motor Drives

Elektrische Eigenschaften

- Erweiterte Sperrschichttemperatur $T_{vj\ op}$
- Niedriges V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$

Electrical Features

- Extended Operation Temperature $T_{vj\ op}$
- Low V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$

Mechanische Eigenschaften

- 4 kV AC 1min Isolationsfestigkeit
- Gehäuse mit CTI > 400
- Große Luft- und Kriechstrecken
- Hohe Leistungsdichte
- IHM B Gehäuse
- Kupferbodenplatte

Mechanical Features

- 4 kV AC 1min Insulation
- Package with CTI > 400
- High Creepage and Clearance Distances
- High Power Density
- IHM B Housing
- Copper Base Plate

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: WB	date of publication: 2013-11-11	
approved by: PL	revision: 2.2	UL approved (E83335)



**Vorläufige Daten
Preliminary Data**

**IGBT, Wechselrichter / IGBT, Inverter
Höchstzulässige Werte / Maximum Rated Values**

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	3600	A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	7200	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	P_{tot}	21,0	kW
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		V_{GES}	+/-20	V

Charakteristische Werte / Characteristic Values

			min.	typ.	max.		
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 3600\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 3600\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 3600\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,90 2,30 2,40	2,25	V V V	
Gate-Schwellenspannung Gate threshold voltage	$I_C = 145\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,2	5,8	6,4	V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		Q_G	38,0			μC
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	0,54			Ω
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	295			nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	9,50			nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}			5,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}			400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 3600\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 0,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,66 0,74 0,78			μs μs μs
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 3600\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 0,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,28 0,29 0,295			μs μs μs
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 3600\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 0,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	1,60 1,70 1,75			μs μs μs
Fallzeit, induktive Last Fall time, inductive load	$I_C = 3600\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 0,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,21 0,315 0,345			μs μs μs
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 3600\text{ A}, V_{CE} = 900\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 12000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 0,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	650 800 900			mJ mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 3600\text{ A}, V_{CE} = 900\text{ V}, L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 2350\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 0,5\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	1200 1450 1500			mJ mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 1000\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	14000			A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		R_{thJC}			7,20	K/kW
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}			6,30	K/kW
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

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